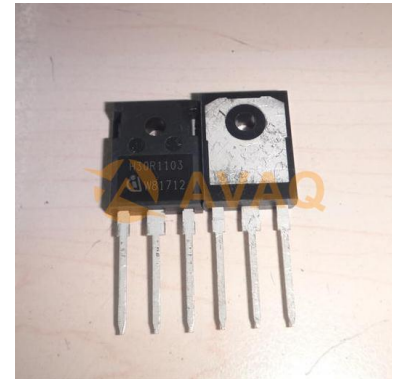


Trans IGBT Chip N-CH 1100V 60A 333mW 3-Pin(3+Tab) TO-247 Tube



Images are for reference only

[Inquiry](#)

Manufacturer: [Infineon Technologies Corporation](#)

Package/Case: TO-247

Product Type: Thyristors

RoHS: RoHS Compliant/Lead free 

Lifecycle: LTB

General Description

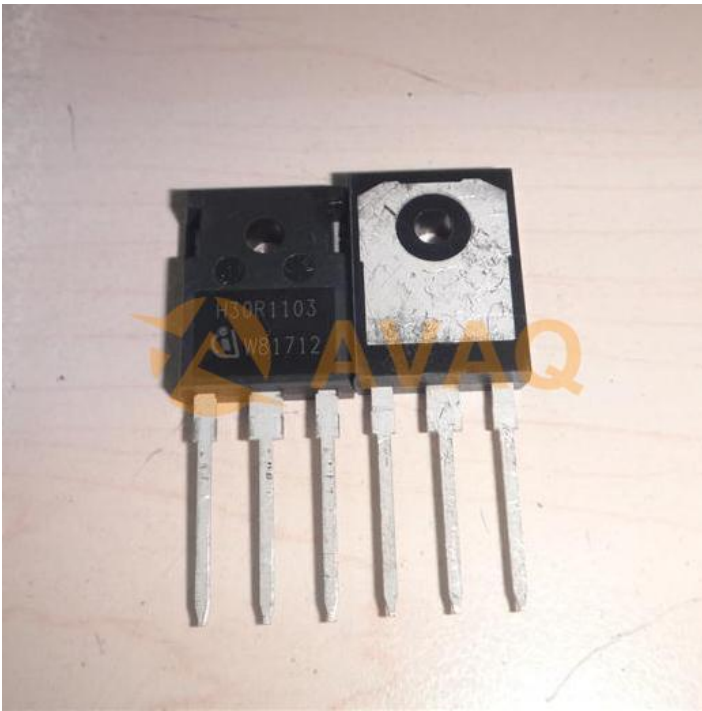
IHW30N110R3 is a part number for an Insulated Gate Bipolar Transistor (IGBT) manufactured by Infineon Technologies.

Key Features

- High collector-emitter voltage (VCE) rating of 1100V
- High collector current (IC) rating of 48A
- Low saturation voltage for reduced power dissipation
- Fast switching speed for high-frequency operation
- Integrated temperature monitoring for thermal protection
- Isolated package for high voltage applications

Application

- Motor control in electric vehicles
- Industrial drives and robotics
- Power supplies and UPS systems
- Renewable energy systems such as wind and solar inverters
- High voltage DC transmission systems



Recommended For You

IHW30N160R2

Infineon Technologies Corporation

TO-247

IHW20N135R3

Infineon Technologies Corporation

TO-247

IHW15N120R3

Infineon Technologies Corporation

TO-247

IHW20N135R5XKSA1

Infineon Technologies Corporation

TO-247

IHW25N120E1

Infineon Technologies Corporation

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IHW20N120R5

Infineon Technologies Corporation

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IHW20N135R5

Infineon Technologies Corporation

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IHW50N65R5

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IHW30N135R5

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IHW40N120R3

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IHW40N60R

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IHW40T60

Infineon Technologies Corporation

TO-247

IHW30N60T

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IHW40N120R5XKSA1

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IHW30N160R5XKSA1

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